

# Information note

INF224202

With this Infineon Technologies AG Information Note we would like to inform you about the following

Datasheet updates to select 4-Mbit to 8-Mbit EXCELON™ F-RAM products with inrush current control



On 16 April 2020, Infineon acquired Cypress.

We are now in the process of merging and consolidating our tools and processes for (infineon + Seypress PCN, Information Notes, Errata and Product Discontinuance. For further details, please visit our website:

https://www.infineon.com/cms/en/about-infineon/company/cypress-acquisition/

Cypress Semiconductor Corporation - An Infineon Technologies AG company, 198 Champion Court San Jose, CA 95134. Tel: (408) 943-2600



### Products affected

Please refer to attached affected product list [23]

### Detailed change information

**Subject** This information note is to inform customers about datasheet updates to the Write protect (WP) pin on select 4-Mbit to 8-Mbit EXCELON™ F-RAM products with inrush current control. The update excludes internal weak pull up configuration on the  $\overline{WP}$  and  $\overline{RESET}$  pins; therefore, it recommends that these two pins be tied to V<sub>DD</sub> if not used and specifies  $\overline{WP} = V_{DD}$  as a test condition for the peak current from  $V_{DD}$  at power-up (IPEAK) measurement.

**Reason** The datasheets have been updated to match the device specifications and actual F-RAM performance.

New

### Description Old

- WP: This pin has an internal weak pull up resistor which keeps this pin HIGH if left floating (not connected on the board). This pin can also be tied to V<sub>DD</sub> if not used.
- IPEAK test condition: VDD = 1.71 V to 1.89 V (or) 1.8 V to 3.6 V.  $\overline{CS} = V_{DD}$ . All other inputs V<sub>SS</sub> or V<sub>DD</sub>. Averaged over 10 µs.
- WP: This pin must be tied to V<sub>DD</sub> if not used.
- $I_{PEAK}$  test condition:  $V_{DD} = 1.71$ V to 1.89 V (or) 1.8 V to 3.6 V.  $\overline{\text{CS}} = V_{DD}$ ,  $\overline{\text{WP}} = V_{DD}$ . All other inputs V<sub>SS</sub> or V<sub>DD</sub>. Averaged over 10 µs.

### Product identification

Infineon maintains traceability of product to wafer level, including wafer fabrication location, through the lot number marked on the package.

## Impact of change

There is no change to the product. Infineon recommends that customers take this opportunity to review these changes against current application notes, system design considerations and customer environment conditions to assess impact (if any) to their application.

Attachments

Affected product list [23]

Intended start of delivery

Effective immediately on release of this information note.

If you have any questions, please do not hesitate to contact your local sales office.

[INFORMATION NOTE] N° [INF224202] Datasheet updates to select 4-Mbit to 8-Mbit EXCELON™ F-RAM products with inrush current control



Item	Marketing Part Number	Family	Datasheet specification
1	CY15B104QI-20LPXC	F-RAM	002-18671
2	600139996	F-RAM	002-30884
3	CG10245AT	F-RAM	002-18148
4	CG10245ATT	F-RAM	002-18148
5	CY15B104QI-20LPXCT	F-RAM	002-18671
6	CY15B104QI-20LPXI	F-RAM	002-18671
7	CY15B104QI-20LPXIT	F-RAM	002-18671
8	CY15B108QI-20LPXA	F-RAM	002-30884
9	CY15B108QI-20LPXAT	F-RAM	002-30884
10	CY15B108QI-20LPXC	F-RAM	002-18148
11	CY15B108QI-20LPXCT	F-RAM	002-18148
12	CY15B108QI-20LPXI	F-RAM	002-18148
13	CY15B108QI-20LPXIT	F-RAM	002-18148
14	CY15B204QI-20LPXI	F-RAM	002-31565
15	CY15V104QI-20LPXC	F-RAM	002-18671
16	CY15V104QI-20LPXCT	F-RAM	002-18671
17	CY15V104QI-20LPXI	F-RAM	002-18671
18	CY15V104QI-20LPXIT	F-RAM	002-18671
19	CY15V108QI-20LPXC	F-RAM	002-18148
20	CY15V108QI-20LPXCT	F-RAM	002-18148
21	CY15V108QI-20LPXI	F-RAM	002-18148
22	CY15V108QI-20LPXIT	F-RAM	002-18148
23	M810078A001	F-RAM	002-29981